

IN THE SPECIFICATION

Please rewrite the paragraph on page 7, lines 5-15, as follows:

14 The present invention provides a semiconductor device including a silicon substrate, and a bipolar transistor having a collector well having a first conductivity-type, an intrinsic base region having a second conductivity-type and received in the collector well and an emitter region having the first conductivity-type and received in the intrinsic base region, a first annular isolation trench encircling the collector well, a second annular isolation trench encircling the first annular isolation trench, and an annular diffused region disposed between the first annular isolation trench and the second isolation trench while being in contact with the first and second isolation trenches.

Please rewrite the paragraph on page 14, lines 1-11, as follows:

24 The first annular isolation trench 20b for the NPN bipolar transistor 12 encircles an n-well or collector well 22 constituting the collector region of the NPN transistor 12. For the NPN bipolar transistor 12, an annular p-well 21 is disposed between the first annular isolation trench 20a and the second annular isolation trench 20b for encircling the collector well 22. The p-well 21 functions for isolation by forming a p-n junction between the same and the collector well 22. The annular p-well 21 has an inner edge defined by the outer edge of the first annular isolation trench 20a and an outer edge defined by the inner edge of the second annular isolation trench 20b.